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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XFI

Product Status	Obsolete
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	CANbus, I ² C, SCI, SPI, USB OTG
Peripherals	LVD, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K × 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-QFP
Supplier Device Package	64-QFP (14x14)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcf51jm64evqh

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



1.3 Features

Table 2 describes the functional units of the MCF51JM128 series.

Unit	Function
CF1CORE (V1 ColdFire core)	Executes programs and interrupt handlers
BDM (background debug module)	Provides a single-pin debugging interface (part of the V1 ColdFire core)
DBG (debug)	Provides debugging and emulation capabilities (part of the V1 ColdFire core)
SYSCTL (system control)	Provides LVD, COP, external interrupt request, and so on
FLASH (flash memory)	Provides storage for program code and constants
RAM (random-access memory)	Provides storage for program code, constants, and variables
RGPIO (rapid general-purpose input/output)	Allows I/O port access at CPU clock speeds
VREG (voltage regulator)	Controls power management throughout the device
USBOTG (USB On-The-Go)	Supports the USB On-The-Go dual-role controller
ADC (analog-to-digital converter)	Measures analog voltages at up to 12 bits of resolution
TPM1, TPM2 (timer/pulse-width modulators)	Provide a variety of timing-based features
CF1_INTC (interrupt controller)	Controls and prioritizes all device interrupts
CAU (cryptographic acceleration unit)	Co-processor support for DES, 3DES, AES, MD5, and SHA-1
RNGA (random number generator accelerator)	32-bit random number generator that complies with FIPS-140
RTC (real-time counter)	Provides a constant-time base with optional interrupt
ACMP (analog comparator)	Compares two analog inputs
CMT (carrier modulator timer)	Infrared output used for the Remote Controller
IIC1, IIC2 (inter-integrated circuits)	Supports the standard IIC communications protocol
KBI (keyboard interrupt)	Provides pin interrupt capabilities
MCG (multipurpose clock generator)	Provides clocking options for the device, including a phase-locked loop (PLL) and frequency-locked loop (FLL) for multiplying slower reference clock sources
XOSC (crystal oscillator)	Supports low/high range crystals
CAN (controller area network)	Supports standard CAN communications protocol
SCI1, SCI2 (serial communications interfaces)	Serial communications UARTs that can support RS-232 and LIN protocols
SPI1, SPI2 (serial peripheral interfaces)	Provide a 4-pin synchronous serial interface



1.3.1 Feature List

- 32-bit Version 1 ColdFire Central Processor Unit (CPU)
 - Up to 50.33 MHz at 2.7 V 5.5 V
 - Performance (Dhrystone 2.1):
 - 0.94 Dhrystone 2.1 MIPS per MHz when running from internal RAM
 - 0.76 Dhrystone 2.1 MIPS per MHz when running from flash
 - Implements Instruction Set Revision C (ISA_C)
 - Supports up to 30 peripheral interrupt requests and seven software interrupts
- On-chip memory
 - Up to 128 KB Flash memory with read/program/erase over full operating voltage and temperature range
 - Up to 16 KB static random access memory (RAM)
 - Security circuitry to prevent unauthorized access to RAM and flash contents
- Power-saving modes
 - Two low-power stop plus wait modes
 - Peripheral clock enable register can disable clocks to unused modules, thereby reducing currents; this behavior allows clocks to remain enabled to specific perhipherals in Stop3 mode
 - Very lower power real-time counter for use in run, wait, and stop modes with internal and external clock sources
- Four Clock Source Options
 - Oscillator (XOSC) Loop-control Pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 38.4 kHz or 1 MHz to 16 MHz
 - FLL/PLL controlled by internal or external reference
 - Trimmable internal reference allows 0.2% resolution and 2% deviation
- System protection features
 - Watchdog computer operating properly (COP) reset with option to run from dedicated 1 kHz internal clock source or bus clock
 - Low-voltage detection with reset or interrupt; selectable trip points
 - Illegal opcode and illegal address detection with programmable reset or exception response
 - Flash block protection
- Debug support
 - Single-wire Background debug interface
 - 4 Program Counters plus two address (optional data) breakpoint registers with programmable 1- or 2-level trigger response
 - 64-entry processor status and debug data trace buffer with programmable start/stop conditions
- Universal Serial Bus (USB) On-The-Go dual-role controller
 - Full-speed USB device controller
 - Fully compliant with USB specification 1.1 and 2.0
 - 16 bidirectional endpoints, with double buffering to provide the maximum throughput
 - Supports control, bulk, interrupt, and isochronous endpoints
 - Supports bus-powered capability with low-power consumption
 - Full-speed / low-speed host controller
 - Host mode allows control, bulk, interrupt, and isochronous transfers
 - OTG protocol logic
 - On-chip USB transceiver
 - On-chip 3.3 V USB regulator and pull-up resistors save system cost

- RTC
 - 8-bit modulus counter with binary- or decimal-based prescaler
 - External clock source for precise time base, time-of-day, calendar or task scheduling functions
 - Free running on-chip low power oscillator (1 kHz) for cyclic wake-up without external components
- Carrier modulator timer (CMT)
 - carrier generator, modulator, and transmitter drive the infrared out (IRO) pin
 - operation in independent high/low time control, baseband, FSK, and direct IRO control modes
- Input/Output
 - 66 GPIOs
 - Eight keyboard interrupt pins with selectable polarity
 - Hysteresis and configurable pull-up device on all input pins; configurable slew rate and drive strength on all output pins
 - 16 bits of Rapid GPIO connected to the processor's local 32-bit platform bus with set, clear, and faster toggle functionality

1.4 Part Numbers

Table 3. Orderable Part Number Summary

Freescale Part Number	Description	Flash / SRAM (KB)	Package	Temperature
MCF51JM128EVLK	MCF51JM128 ColdFire Microcontroller with CAU and RNGA Enabled	128 / 16	80 LQFP	–40 to +105 °C
MCF51JM128VLK	MCF51JM128 ColdFire Microcontroller	128 / 16	80 LQFP	–40 to +105 °C
MCF51JM128EVLH	MCF51JM128 ColdFire Microcontroller with CAU and RNGA Enabled	128 / 16	64 LQFP	–40 to +105 °C
MCF51JM128VLH	MCF51JM128 ColdFire Microcontroller	128 / 16	64 LQFP	–40 to +105 °C
MCF51JM128EVQH MCF51JM128 ColdFire Microcontroller with CAU and RNGA Enabled		128 / 16	64 QFP	–40 to +105 °C
MCF51JM128VQH	MCF51JM128 ColdFire Microcontroller	128 / 16	64 QFP	–40 to +105 °C
MCF51JM128EVLD	MCF51JM128 ColdFire Microcontroller with CAU and RNGA Enabled	128 / 16	44 LQFP	–40 to +105 °C
MCF51JM128VLD	MCF51JM128 ColdFire Microcontroller	128 / 16	44 LQFP	–40 to +105 °C
MCF51JM64EVLK	MCF51JM64 ColdFire Microcontroller with CAU and RNGA Enabled	64 / 16	80 LQFP	–40 to +105 °C
MCF51JM64VLK	MCF51JM64 ColdFire Microcontroller	64 / 16	80 LQFP	–40 to +105 °C
MCF51JM64EVLH	MCF51JM64 ColdFire Microcontroller with CAU and RNGA Enabled	64 / 16	64 LQFP	–40 to +105 °C
MCF51JM64VLH	MCF51JM64 ColdFire Microcontroller	64 / 16	64 LQFP	–40 to +105 °C
MCF51JM64EVQH	MCF51JM64 ColdFire Microcontroller with CAU and RNGA Enabled	64 / 16	64 QFP	−40 to +105 °C
MCF51JM64VQH	MCF51JM64 ColdFire Microcontroller	64 / 16	64 QFP	–40 to +105 °C

Figure 4 shows the pinout of the 44-pin LQFP.

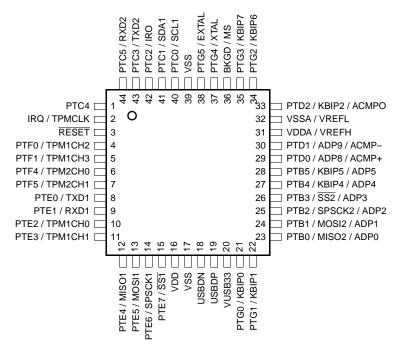


Figure 4. 44-pin LQFP

Table 4 shows the package pin assignments.

Pin	Num	ber	< Lowest Priority > Highest			
80	64	44	Port Pin	Alt 1	Alt 2	
1	1	1	PTC4		_	
2	2	2	_	IRQ	TPMCLK	
3	3	3	—	RESET	_	
4	4	4	PTF0	TPM1CH2	_	
5	5	5	PTF1	TPM1CH3	_	
6	6	_	PTF2	TPM1CH4	_	
7	7		PTF3	TPM1CH5	_	
8	8	6	PTF4	TPM2CH0	BUSCLK_OUT	
9	9		PTC6	RXCAN	—	
10	10	—	PTF7	TXCAN	_	
11	11	7	PTF5	TPM2CH1	_	
12	12	_	PTF6	—	—	
13	13	8	PTE0	TXD1	_	
14	14	9	PTE1	RXD1		
15	15	10	PTE2	TPM1CH0		



2 **Preliminary Electrical Characteristics**

This section contains electrical specification tables and reference timing diagrams for the MCF51JM128 microcontroller, including detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications.

The electrical specifications are preliminary and are from previous designs or design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. These specifications will, however, be met for production silicon. Finalized specifications will be published after complete characterization and device qualifications have been completed.

NOTE

The parameters specified in this data sheet supersede any values found in the module specifications.

2.1 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 5.	. Parameter Classifications	

Р	Those parameters are guaranteed during production testing on each individual device.
с	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled C in the parameter tables where appropriate.

2.2 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 6 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, V_{SS} or V_{DD}).



- ³ 1s Single Layer Board, one signal layer
- ⁴ 2s2p Four Layer Board, 2 signal and 2 power layers

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA})$$
 Eqn. 1

where:

 T_A = Ambient temperature, $^{\circ}C\theta_{JA}$ = Package thermal resistance, junction-to-ambient, $^{\circ}C/WP_D = P_{int} + P_{I/O}P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power $P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} \ll P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_{D} = K \div (T_{J} + 273^{\circ}C)$$
 Eqn. 2

Solving equations 1 and 2 for K gives:

$$K = P_D \times (T_A + 273^{\circ}C) + \theta_{JA} \times (P_D)^2$$
 Eqn. 3

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A . Using this value of K, the values of P_D and T_J can be obtained by solving equations 1 and 2 iteratively for any value of T_A .

2.4 Electrostatic Discharge (ESD) Protection Characteristics

Although damage from static discharge is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with CDF-AEC-Q00 Stress Test Qualification for Automotive Grade Integrated Circuits. (http://www.aecouncil.com/) This device was qualified to AEC-Q100 Rev E.

A device is considered to have failed if, after exposure to ESD pulses, the device no longer meets the device specification requirements. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Model Description		Symbol	Value	Unit
	Series Resistance	R1	1500	Ω
Human Body	Storage Capacitance	С	100	pF
	Number of Pulse per pin	_	3	
Latch-up	Minimum input voltage limit		-2.5	V
	Maximum input voltage limit		7.5	V

Table 8. ESD and Latch-up Test Conditions



Preliminary Electrical Characteristics

Num	С	Parameter		Symbol	V _{DD} (V)	Typical ¹	Max ²	Unit
4 C	Wait mode supply current ³ measured at (CPU	(CPU		5	2.03	3		
	clock = 2 MHz, f _{Bus} = 1 MHz)			3	2	3	mA	
5	С		(CPU	WI _{DD}	5	7.73	12	_
		clock = 16 MHz, f _{Bus} = 8 MHz)			3	7.7	12	mA
6	С	Wait mode supply current ³ measured at	(CPU		5	22	30	
		clock = 48 MHz, f _{Bus} = 24 MHz)			3	21.9	30	mA
7	7 C Stop2 mode supply current		–40 °C 25 °C 105 °C	S2I _{DD}	5	1.35	3 3 35	μΑ
		–40 °C 25 °C 105 °C	טט	3	1.25	3 3 35	μΑ	
8 P	25 °(105 °(-40 °(25 °(–40 ℃ 25 ℃ 105 ℃	S3I _{DD}	5	1.41	3 3 35	μΑ	
		–40 °C 25 °C 105 °C	UUI _{DD}	3	1.35	3 3 35	μΑ	
9	С	Stop4 mode supply current	–40 °C 25 °C 105 °C	S4I _{DD}	5	106	200	μΑ
	25 °C	-40 ℃ 25 ℃ 105 ℃	טט	3	96	200	μΑ	
10	Р	P RTC adder to stop2 or stop3 ⁴ , 25°C		0001	5	300	—	nA
				S23I _{DDRTC}	3	300		nA
11	Р	Adder to stop3 for oscillator enabled ⁵		S23I _{DDOSC}	5	5		μΑ
		(ERCLKEN =1 and EREFSTEN = 1)			3	5	_	μA

Table 11.	Supply	Current	Characteristics
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¹ Typicals are measured at 25°C.

² Values given here are preliminary estimates prior to completing characterization.

³ All modules' clocks are switched on, code runs from flash, in FEI mode, and there are no DC loads on port pins.

⁴ Most customers are expected to find that auto-wakeup from stop2 or stop3 can be used instead of the higher current wait mode.

⁵ Values given under the following conditions: low range operation (RANGE = 0), low power mode (HGO = 0)



2.7 Analog Comparator (ACMP) Electricals

Num	С	Rating	Symbol	Min	Typical	Мах	Unit
1		Supply voltage	V _{DD}	2.7	—	5.5	V
2		Supply current (active)	I _{DDAC}	—	20	35	μΑ
3		Analog input voltage	V _{AIN}	$V_{SS} - 0.3$		V _{DD}	V
4		Analog input offset voltage	V _{AIO}		20	40	mV
5		Analog Comparator hysteresis	V _H	3.0	6.0	20.0	mV
6		Analog input leakage current	I _{ALKG}			1.0	μΑ
7		Analog Comparator initialization delay	t _{AINIT}	—		1.0	μS
8		Bandgap Voltage Reference Factory trimmed at V _{DD} = 3.0 V, Temp = 25°C	V _{BG}	1.19	1.20	1.21	V

2.8 ADC Characteristics

Characteristic	Conditions	Symb	Min	Typ ¹	Max	Unit	Comment
Supply voltage	Absolute	V _{DDA}	2.7	_	5.5	V	
	Delta to V _{DD} (V _{DD} -V _{DDA}) ²	ΔV_{DDA}	-100	0	+100	mV	
Ground voltage	Delta to V _{SS} (V _{SS} -V _{SSA}) ²	ΔV_{SSA}	-100	0	+100	mV	
Ref Voltage High		V _{REFH}	2.7	V _{DDA}	V _{DDA}	V	
Ref Voltage Low		V _{REFL}	V _{SSA}	V _{SSA}	V _{SSA}	V	
Input Voltage		V _{ADIN}	V _{REFL}	_	V _{REFH}	V	
Input Capacitance		C _{ADIN}	_	4.5	5.5	pF	
Input Resistance		R _{ADIN}	—	3	5	kΩ	
Analog Source Resistance	12 bit mode f _{ADCK} > 4MHz f _{ADCK} < 4MHz	R _{AS}	_		2 5	kΩ	External to MCU
	10 bit mode f _{ADCK} > 4MHz f _{ADCK} < 4MHz		_	_	5 10		
	8 bit mode (all valid f _{ADCK})	1	—	—	10		
ADC Conversion	High Speed (ADLPC=0)	f _{ADCK}	0.4		8.0	MHz	
Clock Freq.	Low Power (ADLPC=1)		0.4	—	4.0		

¹ Typical values assume V_{DDA} = 5.0V, Temp = 25°C, f_{ADCK}=1.0MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

² DC potential difference.

2.10 MCG Specifications

Table 16. MCG Frequency Specifications (Temperature Range = -40 to 125°C Ambient)

Num	С	Rati	ng	Symbol	Min	Typical ¹	Max	Unit
1	Ρ	Internal reference frequence = 5 V and temperature = 25		f _{int_ft}	_	32.768	—	kHz
2	Ρ	Average internal reference	frequency – untrimmed	f _{int_ut}	31.25		39.0625	kHz
3	Т	Internal reference startup ti	me	t _{irefst}	—	60	100	μs
	Ρ	DCO output frequency	Low range (DRS=00)		16	_	20	
4	Ρ	range - untrimmed ²	Mid range (DRS=01)	f _{dco_ut}	32	_	40	MHz
	Ρ		High range (DRS=10)		48		60	
	Ρ	DCO output frequency ²	Low range (DRS=00)		—	19.92	—	
5	Ρ	Reference =32768Hz	Mid range (DRS=01)	f _{dco_DMX32}	—	39.85	—	MHz
	Ρ	and DMX32 = 1	High range (DRS=10)		—	59.77	—	
6	D	Resolution of trimmed DCC voltage and temperature (u	,	$\Delta f_{dco_res_t}$	—	±0.1	±0.2	%f _{dco}
7	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco_res_t}$	_	±0.2	±0.4	%f _{dco}
8	D	Total deviation of trimmed DCO output frequency over voltage and temperature		Δf_{dco_t}	—	0.5 -1.0	±2	%f _{dco}
9	D	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of $0 - 70 ^{\circ}\text{C}$		Δf_{dco_t}	—	±0.5	±1	%f _{dco}
10	D	FLL acquisition time ³		t _{fll_acquire}	—	_	1	ms
11	D	PLL acquisition time ⁴		t _{pll_acquire}	—	_	1	ms
12	D	Long term Jitter of DCO ou 2ms interval) ⁵	put clock (averaged over	C _{Jitter}	_	0.02	0.2	%f _{dco}
13	D	VCO operating frequency		f _{vco}	7.0	_	55.0	MHz
14	D	Jitter of PLL output clock m		f _{pll_jitter_625ns}	—	0.566 ⁵	—	%f _{pll}
15	D	Lock entry frequency tolera		D _{lock}	±1.49	_	±2.98	%
16	D	Lock exit frequency tolerand	ce ⁸	D _{unl}	±4.47	_	±5.97	%
17	D	Lock time — FLL		t _{fll_lock}	_	_	t _{fll_acquire+} 1075(1/fint_t)	S
18	D	Lock time — PLL		t _{pll_lock}	_	_	t _{pll_acquire+} 1075(1/ ^f pll_r ef)	S
19	D	Loss of external clock minir = 0	num frequency – RANGE	f _{loc_low}	(3/5) x f _{int}	_	—	kHz

¹ Data in Typical column was characterized at 5.0 V, 25C or is typical recommended value

² The resulting bus clock frequency should not exceed the maximum specified bus clock frequency of the device.

³ This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

⁴ This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.



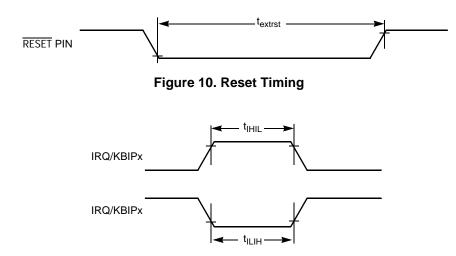


Figure 11. IRQ/KBIPx Timing

2.11.2 Timer/PWM (TPM) Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

NUM	С	Function	Symbol	Min	Max	Unit
1		External clock frequency	f _{TPMext}	dc	f _{Bus} /4	MHz
2	_	External clock period	t _{TPMext}	4	_	t _{cyc}
3	D	External clock high time	t _{clkh}	1.5		t _{cyc}
4	D	External clock low time	t _{clkl}	1.5	_	t _{cyc}
5	D	Input capture pulse width	t _{ICPW}	1.5	_	t _{cyc}

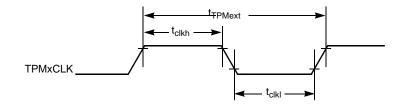


Figure 12. Timer External Clock



2.12 SPI Characteristics

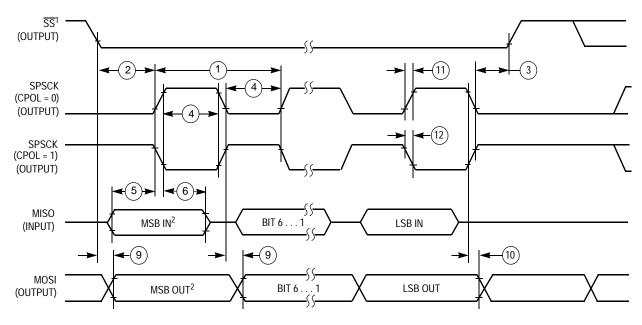
Table 20 and Figure 14 through Figure 17 describe the timing requirements for the SPI system.

No.	С	Function	Symbol	Min	Max	Unit
_	D	Operating frequency Master Slave	f _{op}	f _{Bus} /2048 0	f _{Bus} /2 f _{Bus} /4	Hz
1	D	SPSCK period Master Slave	t _{SPSCK}	2 4	2048 —	t _{cyc} t _{cyc}
2	D	Enable lead time Master Slave	t _{Lead}	1/2 1		t _{SPSCK} t _{cyc}
3	D	Enable lag time Master Slave	t _{Lag}	1/2 1		t _{SPSCK} t _{сус}
4	D	Clock (SPSCK) high or low time Master Slave	t _{WSPSCK}	$t_{cyc} - 30$ $t_{cyc} - 30$	1024 t _{cyc}	ns ns
5	D	Data setup time (inputs) Master Slave	t _{SU}	15 15		ns ns
6	D	Data hold time (inputs) Master Slave	t _{HI}	0 25	_	ns ns
7	D	Slave access time	t _a	—	1	t _{cyc}
8	D	Slave MISO disable time	t _{dis}	—	1	t _{cyc}
9	D	Data valid (after SPSCK edge) Master Slave	t _v		25 25	ns ns
10	D	Data hold time (outputs) Master Slave	t _{HO}	0 0		ns ns
11	D	Rise time Input Output	t _{RI} t _{RO}	_	t _{cyc} – 25 25	ns ns
12	D	Fall time Input Output	t _{FI} t _{FO}		t _{cyc} – 25 25	ns ns

Table 20. SPI Timing



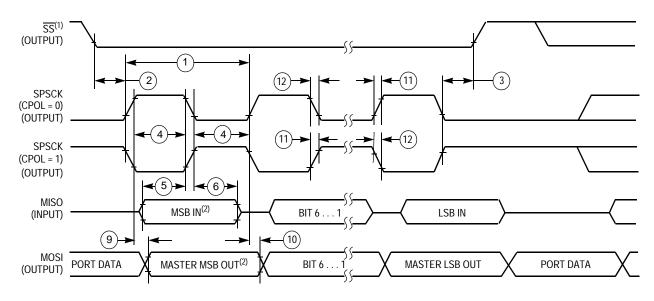
Preliminary Electrical Characteristics



NOTES:

- 1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI Master Timing (CPHA = 0)



NOTES:

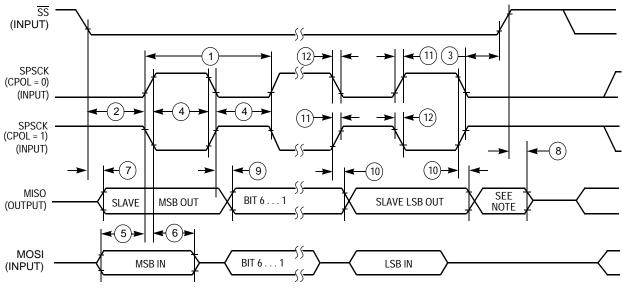
1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 15. SPI Master Timing (CPHA = 1)

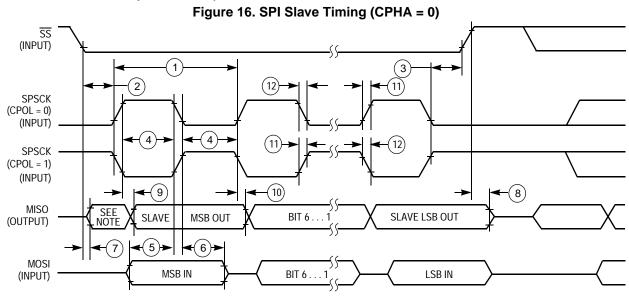


Preliminary Electrical Characteristics



NOTE:

1. Not defined but normally MSB of character just received



NOTE:

1. Not defined but normally LSB of character just received





Preliminary Electrical Characteristics

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply.

Num	С	Characteristic	Symbol	Min	Typ ¹	Max	Unit
1		Supply voltage for program/erase	V _{prog/erase}	2.7		5.5	V
2		Supply voltage for read operation	V _{Read}	2.7		5.5	V
3		Internal FCLK frequency ²	f _{FCLK}	150		200	kHz
4		Internal FCLK period (1/FCLK)	t _{Fcyc}	5		6.67	μs
5		Byte program time (random location) ⁽²⁾	t _{prog}	9			t _{Fcyc}
6		Byte program time (burst mode) ⁽²⁾	t _{Burst}	4			t _{Fcyc}
7		Page erase time ³	t _{Page}	4000			t _{Fcyc}
8		Mass erase time ⁽²⁾	t _{Mass}	20,000			t _{Fcyc}
9	с	Program/erase endurance ⁴ T _L to T _H = -40° C to + 105° C T = 25° C		10,000	 100,000		cycles
10		Data retention ⁵	t _{D_ret}	15	100	_	years

¹ Typical values are based on characterization data at $V_{DD} = 5.0 \text{ V}$, 25°C unless otherwise stated.

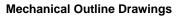
² The frequency of this clock is controlled by a software setting.

- ³ These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.
- ⁴ Typical endurance for Flash was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory*.
- ⁵ Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, Typical Data Retention for Nonvolatile Memory.

2.14 USB Electricals

The USB electricals for the USBOTG module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit http://www.usb.org.

If the Freescale USBOTG implementation requires additional or deviant electrical characteristics, this space would be used to communicate that information.



	MECHANICAL OUTLINES		DOCUMENT NO: 98ASS23234W				
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NOTES:							
1. DIMENSIONS ARE IN M	ILLIMETERS.						
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.							
3. DATUMS A, B AND D T	O BE DETERMINE	D AT DATUM PLA	ANE H.				
A DIMENSIONS TO BE DE	TERMINED AT SE	ATING PLANE C.					
THIS DIMENSION DOES PROTRUSION SHALL NO BY MORE THAN 0.08 m LOCATED ON THE LOWE PROTRUSION AND ADJA	T CAUSE THE LE m AT MAXIMUM M R RADIUS OR TH	AD WIDTH TO E> ATERIAL CONDIT E FOOT. MINIMU	KCEED TH FION. DA JM SPACE	HE UPPER LIMIT AMBAR CANNOT BE E BETWEEN			
A THIS DIMENSION DOES IS 0.25 mm PER SIDE DIMENSION INCLUDING	. THIS DIMENSI	ON IS MAXIMUM					
\triangle exact shape of each	CORNER IS OPT	IONAL.					
THESE DIMENSIONS AP			THE LEAD	DBETWEEN			
TITLE: 64LD LQFP	,	CASE NUMBER: 840F-02					
10 X 10 X 1.4	PKG,	STANDARD: JEDEC MS-026 BCD					
0.5 PITCH, CASE	UUILINE	PACKAGE CODE:	8426	SHEET: 3			

Figure 23. 64-pin LQFP Diagram - III

MCF51JM128 ColdFire Microcontroller, Rev. 4

NP



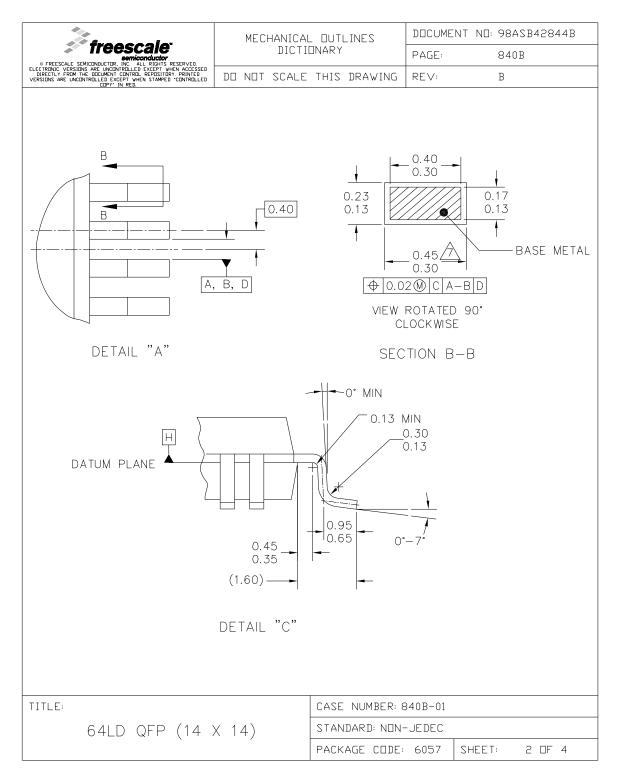


Figure 25. 64-pin QFP Diagram - II

Mechanical Outline Drawings

N

		LOUTLINES	DOCUME	INT NO: 98ASB42844B		
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NOTES:						
		14 514 1004				
1. DIMENSIONING AND TOLERANC		14.5M, 1994.				
2. CONTROLLING DIMENSION: MIL	LIMETER.					
3. DATUM PLANE -H- IS LOCA WHERE THE LEAD EXITS THE						
4. DATUMS A-B AND -D- TO	be deterMined A	T DATUM PLANE	-H			
DIMENSIONS TO BE DETERMIN	ED AT SEATING F	PLANE -C				
DIMENSIONS DO NOT INCLUDE SIDE. DIMENSIONS DO INCLUE	MOLD PROTRUSI DE MOLD MISMATC	ON. ALLOWABLE F Ch and are dete	ROTRUSI	ON IS 0.25mm PER AT DATUM PLANE —H—.		
A DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08mm TOTAL IN EXCESS OF THE DIMENSION AT MAXIMUM MATERIAL CONDICTION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.						
TITLE:		CASE NUMBER: 8	340B-01			
64LD QFP (14 X	14)	STANDARD: NON-	-JEDEC			
		PACKAGE CODE:	6057	SHEET: 3 OF 4		

Figure 26. 64-pin QFP Diagram - III



	MECHANICA	_ DUTLINES	DOCUMENT NO: 98ASS23225						
		DNARY	PAGE:	824D					
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NOTES:									
1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M-1994.									
2. CONTROLLING DIMENSION: MILLIMETER									
3. DATUM PLANE H IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.									
4. DATUMS L, M AND N TO E	be determined a	t datum plane	Н.						
5. DIMENSIONS TO BE DETERI	MINED AT SEATING	G PLANE T.							
6. DIMENSIONS DO NOT INCLU SIDE. DIMENSIONS DO INCI PLANE H.					PER				
<u> </u>) EXCEED 0.53. M								
TITLE:		CASE NUMBER: 824D-02							
44 LD LQFP, 10 X 10 PKG, 0.8 PITCH,	1.4 THICK	STANDARD: JEDEC MS-026 BCB							
		PACKAGE CODE:	8256	SHEET: 3	DF 4				

Figure 29. 44-pin LQFP Diagram - III



Revision History

4 Revision History

This section lists major changes between versions of the MCF51JM128 Data Sheet document.

Table 23. Changes	Between Revisions
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Revision	Description
1	Updated features list Updated the figures Typical Low-side Drive (sink) characteristics – High Drive (PTxDSn = 1), Typical Low-side Drive (sink) characteristics – Low Drive (PTxDSn = 0), and Typical High-side Drive (source) characteristics – High Drive (PTxDSn = 1) Added the figure Typical High-side Drive (source) characteristics – Low Drive (PTxDSn = 0) Updated the table Supply Current Characteristics Updated the table Oscillator Electrical Specifications (Temperature Range = -40 to 105xC Ambient) Updated the table SPI Electrical Characteristic, DC Characteristics
2	Updated the table Orderable Part Number Summary, DC Characteristics, and Supply Current Characteristics
3	Updated the table Orderable Part Number Summary, MCG Characteristics, SPI Characteristics, and Supply Current Characteristics Changed V _{DDAD} to V _{DDA} , V _{SSAD} to V _{SSA} Updated the table Device comparison
4	 Added "RAM retention voltage" parameter in "DC Characteristics" table, alongwith a table note. Added "Temp sensor voltage" parameter in "5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})" table. Added "Temp sensor slope" parameter in 5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) table. Also, corrected unit of "Temp sensor voltage" parameter in 5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) table. Also, corrected unit of "Temp sensor voltage" parameter in 5 Volt 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) table.

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